

# Thyristor/Thyristor (MAGN-A-PAK Power Modules), 320 A



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PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	320 A					
Туре	Modules - thyristor, standard					
Package	MAGN-A-PAK					

## **FEATURES**

- · High voltage
- · Electrically isolated base plate
- 3600 V<sub>RMS</sub> isolating voltage
- Industrial standard package
- · Simplified mechanical designs, rapid assembly
- · High surge capability
- Large creepage distances
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **DESCRIPTION**

This VSK series of MAGN-A-PAK modules uses high voltage power thyristor/thyristor in doubler circuit configuration. The semiconductors are electrically isolated from the metal base, allowing common heatsinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges or as AC-switches when modules are connected in anti-parallel mode. These modules are intended for general purpose applications such as battery chargers, welders, motor drives, UPS, etc.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I <sub>T(AV)</sub>	70 °C	320					
I <sub>T(RMS)</sub>		710	A				
I <sub>TSM</sub>	50 Hz	9000					
	60 Hz	9420					
I <sup>2</sup> t	50 Hz	405	kA <sup>2</sup> s				
1-1	60 Hz	370	KA-S				
I <sup>2</sup> √t		4050	kA <sup>2√</sup> s				
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 1600	V				
T <sub>J</sub>	Range	-40 to +130	°C				

## **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS										
TYPE NUMBER   VOLTAGE   PEAK REVERSE AND		V <sub>RRM</sub> /V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE BLOCKING VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 130 °C MAXIMUM mA						
VS-VSKT320-	12	1200	1300	50						
V5-V5K132U-	16	1600	1700	50						



PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current		190° conduction	n, half sine wave	320	Α	
at case temperature	I <sub>T(AV)</sub>	180 Conduction	n, nan sine wave		70	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	As AC switch			710	
		t = 10 ms	No voltage		9000	
Maximum peak, one-cycle on-state	<b>L</b>	t = 8.3 ms	reapplied		9420	Α
non-repetitive, surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>	Sinusoidal	7570	
		t = 8.3 ms	reapplied	half wave,	7920	
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	405	- kA <sup>2</sup> s
Maximum 124 for funing	l <sup>2</sup> t	t = 8.3 ms	reapplied	-	370	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		287	
		t = 8.3 ms	reapplied		262	
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 ms to 10	ms, no voltage re	applied	4050	kA²√s
Low level value or threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T_0}$ $I_J = I_J$ maximum	$_{(AV)}$ < I < $\pi$ x $I_{T(AV)}$ , m		0.80	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)}), T_J$	<sub>J</sub> = T <sub>J</sub> maximum		1.03	
Low level value on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $I_{T} = I_{T} =$			0.75	mΩ
High level value on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			11152
Maximum peak on-state or	V V	$I_{TM} = 750 \text{ A}, T_J = 25 ^{\circ}\text{C}, 180^{\circ} \text{ conduction},$ average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$			1.40	V
forward voltage drop	$V_{TM_i}V_{FM_i}$	$I_{TM} = 750 \text{ A}$ , $T_J = T_J \text{ maximum}$ , $180^{\circ}$ conduction, average power = $V_{T(TO)} \times I_{T(AV)} + r_f \times (I_{T(RMS)})^2$			1.37	V
Maximum holding current	I <sub>H</sub>	Anode supply = 12 V, initial $I_T = 30 \text{ A}$ , $T_J = 25 ^{\circ}\text{C}$		500		
Maximum latching current	ΙL		Anode supply = 12 V, resistive load = 1 $\Omega$ , gate pulse: 10 V, 100 $\mu$ s, T, I = 25 °C			mA

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical delay time	t <sub>d</sub>	T <sub>J</sub> = 25 °C, gate current = 1 A dl <sub>α</sub> /dt = 1 A/μs	1.0						
Typical rise time t <sub>r</sub>		$V_{d} = 0.67 \% V_{DRM}$	2.0	μs					
Typical turn-off time range	t <sub>q</sub>	$I_{TM}$ = 300 A; dI/dt = 15 A/ $\mu$ s; $T_J$ = $T_J$ maximum; $V_R$ = 50 V; dV/dt = 20 V/ $\mu$ s; gate 0 V, 100 $\Omega$	200 to 350						

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current	I <sub>RRM,</sub> I <sub>DRM</sub>	$T_J = T_J$ maximum	50	mA				
RMS insulation voltage V <sub>INS</sub>		50 Hz, circuit to base, all terminals shorted, 25 $^{\circ}\text{C}$ , 1 s	3600	V				
Critical rate of rise of off-state voltage dV/dt		$T_J = T_J$ maximum, exponential to 67 % rated $V_{DRM}$	1000	V/µs				



TRIGGERING								
PARAMETER	SYMBOL	TEST C	TEST CONDITIONS		UNITS			
Maximum peak gate power	$P_{GM}$	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	10.0	W			
Maximum average gate power	$P_{G(AV)}$	$f = 50 \text{ Hz}, T_J = T_J \text{ r}$	maximum	2.0	VV			
Maximum peak gate current	+ I <sub>GM</sub>	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	3.0	Α			
Maximum peak negative gate voltage	- V <sub>GT</sub>	$t_p \le 5 \text{ ms}, T_J = T_J r$	maximum	5.0				
		T <sub>J</sub> = - 40 °C	Anode supply = 12 V, resistive load; Ra = 1 $\Omega$	4.0	V			
Maximum required DC gate voltage to trigger	$V_{GT}$	T <sub>J</sub> = 25 °C		3.0				
		T <sub>J</sub> = T <sub>J</sub> maximum	, , , , , , , , , , , , , , , , , , , ,	2.0				
		T <sub>J</sub> = - 40 °C	Anode supply = 12 V, resistive load; Ra = 1 $\Omega$	350				
Maximum required DC gate current to trigger	$I_{GT}$	T <sub>J</sub> = 25 °C		200	mA			
		T <sub>J</sub> = T <sub>J</sub> maximum	10000110 1000, 110 - 1 11	100	1			
Maximum gate voltage that will not trigger	$V_{GD}$	$T_J = T_J$ maximum, rated $V_{DRM}$ applied		0.25	V			
Maximum gate current that will not trigger	I <sub>GD</sub>	$T_J = T_J$ maximum, rated $V_{DRM}$ applied		10.0	mA			
Maximum rate of rise of turned-on current	dl/dt	$T_J = T_J$ maximum, rated $V_{DRM}$ applied		500	A/µs			

THERMAL	THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	R	SYMBOL	MBOL TEST CONDITIONS		UNITS			
	Junction operating and storage temperature range			-40 to +130	°C			
Maximum thermal resistance, junction to case per junction		R <sub>thJC</sub>	DC operation	0.125	K/W			
	Typical thermal resistance, case to heatsink per module		Mounting surface flat, smooth and greased 0.		rv vv			
Mounting	MAGN-A-PAK to heatsink		A mounting compound is recommended and the torque should be rechecked after	4 to 6	Nm			
± 10 %	torque a period of about 3 h		a period of about 3 hours to allow for the spread of the compound.	4 10 0	IVIII			
Approximate weight				500	g			
Approximate weight				17.8	oz.			
Case style				MAGN	-A-PAK			

△R CONDUCTION PER JUNCTION											
DEVICES	SINUS	DIDAL CON	NDUCTION	AT T <sub>J</sub> MA	XIMUM	RECTANGULAR CONDUCTION AT T <sub>J</sub> MAXIMUM					UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSKT320-	0.009	0.010	0.013	0.020	0.032	0.007	0.011	0.015	0.020	0.033	K/W

#### Note

 $\bullet \quad \text{Table shows the increment of thermal resistance } \mathsf{R}_{\text{th}JC} \text{ when devices operate at different conduction angles than } \mathsf{DC}$ 



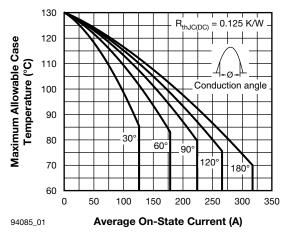


Fig. 1 - Current Ratings Characteristics

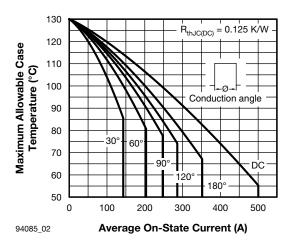


Fig. 2 - Current Ratings Characteristics

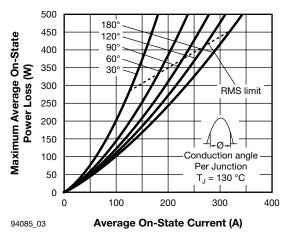


Fig. 3 - On-State Power Loss Characteristics

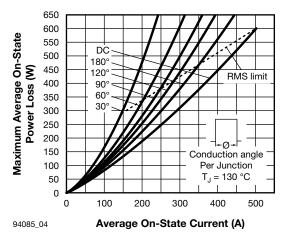


Fig. 4 - On-State Power Loss Characteristics

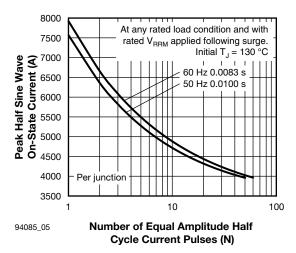


Fig. 5 - Maximum Non-Repetitive Surge Current

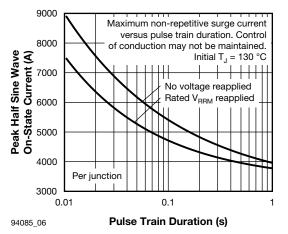


Fig. 6 - Maximum Non-Repetitive Surge Current

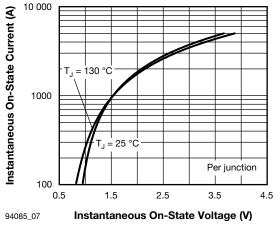


Fig. 7 - On-State Voltage Drop Characteristics

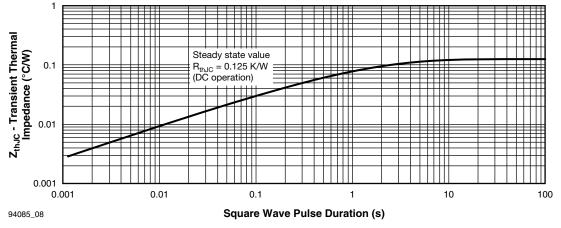
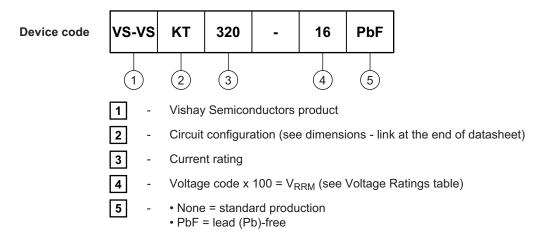


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

## **ORDERING INFORMATION TABLE**



#### Note

• To order the optional hardware go to <a href="www.vishay.com/doc?95172">www.vishay.com/doc?95172</a>



# **VS-VSKT320PbF Series**

# Vishay Semiconductors

CIRCUIT CONFIGURATION						
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Two SCRs doubler circuit	КТ	~				

LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95086



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